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FDC606P

P-Channel 1.8V Specified PowerTrench® MOSFET

General Description

This P-Channel 1.8V specified MOSFET uses Fairchild's low voltage PowerTrench process. It has been optimized for battery power management applications.

Applications

- · Battery management
- Load switch
- · Battery protection

Features

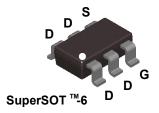
• -6 A, -12 V. R_{DS(ON)}

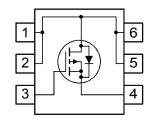
 $R_{DS(ON)}$ = 26 m Ω @ V_{GS} = -4.5 V

 $R_{DS(ON)}$ = 35 m Ω @ V_{GS} = -2.5 V

 $R_{DS(ON)}$ = 53 m Ω @ V_{GS} = -1.8 V

- · Fast switching speed
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-12	V
V_{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	- 6	A
	- Pulsed		-20	
P _D	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T_J , T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
.606	FDC606P	7"	8mm	3000 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1	II.	I.		I.
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = -250 \mu\text{A}$	-12			V
<u>ΔBV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A,Referenced to 25°C		-3		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}$			– 1	μΑ
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.5	-1.5	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A,Referenced to 25°C		2.5		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -6 \text{ A}$ $V_{GS} = -2.5 \text{ V}, I_D = -5 \text{ A}$ $V_{GS} = -1.8 \text{ V}, I_D = -4 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -6 \text{ A}, T_J = 125^{\circ}\text{C}$		21 26 34 28	26 35 53 35	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-20			Α
g FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -6 \text{ A}$		25		S
Dynamio	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -6 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		1699		pF
Coss	Output Capacitance	f = 1.0 MHz		679		pF
C _{rss}	Reverse Transfer Capacitance			423		pF
Switchir	ng Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -6 \text{ V}, \qquad I_D = -1 \text{ A},$		11	19	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		10	20	ns
t _{d(off)}	Turn-Off Delay Time	1		89	142	ns
t _f	Turn-Off Fall Time	1		70	112	ns
Qg	Total Gate Charge	$V_{DS} = -6 \text{ V}, \qquad I_{D} = -6 \text{ A},$		18	25	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		3		nC
Q_{gd}	Gate-Drain Charge			4.2		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source				-1.3	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -1.3 \text{ A} \text{(Note 2)}$		-0.6	-1.2	V

Notes:

- 1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
- a. 78°C/W when mounted on a 1in² pad of 2oz copper on FR-4 board.
- b. 156°C/W when mounted on a minimum pad.
- 2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics

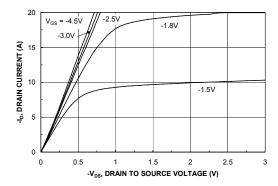
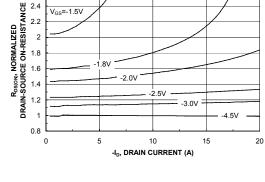


Figure 1. On-Region Characteristics.



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Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

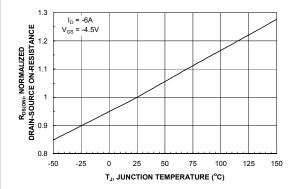


Figure 3. On-Resistance Variation with Temperature.

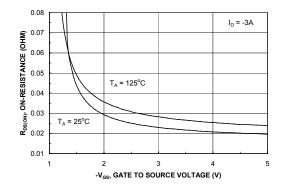


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

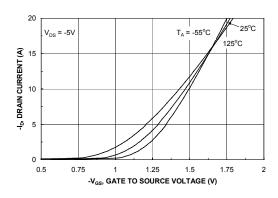


Figure 5. Transfer Characteristics.

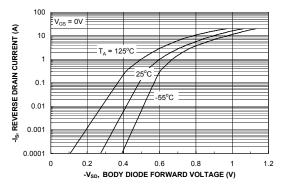
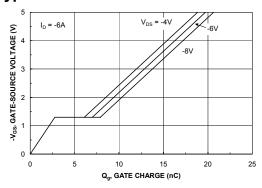


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



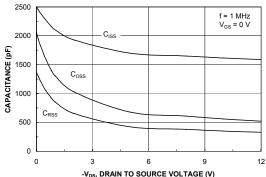
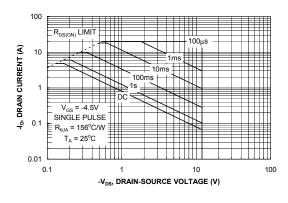


Figure 7. Gate Charge Characteristics.





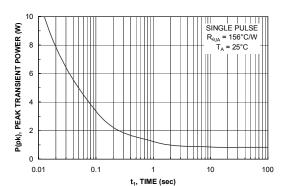


Figure 9. Maximum Safe Operating Area.



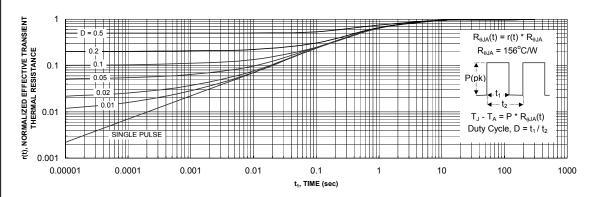


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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